

In the Specification:

Please amend page 9, lines 16 – 24 as follows:

Broadly, one aspect of the present invention pertains to a thin film with a low dielectric constant by co-polymerization of an ethylenic-containing precursor (Ia) with a benzocyclobutane (IIa')-, a biphenyl (IIb')- or a dieneone (IIc')-containing precursor, or their admixture. The ethylenic-containing precursor (Ia) can have the following general structure:



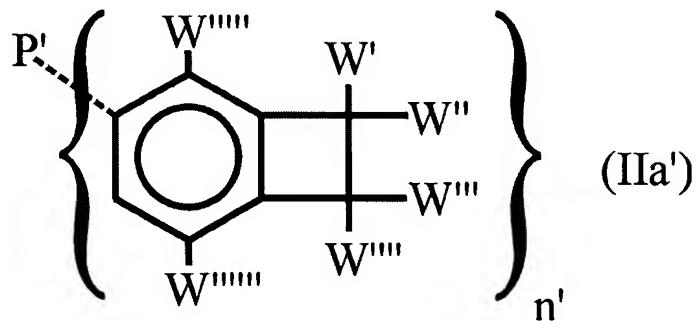
wherein, W is -H, -F or fluorinated phenyl; n° is an integer of at least 2, but is less than total sp^2C substitutions on the aromatic moiety, P, and Z is a moiety containing an ethylenic ($C \equiv C$) group.

Please amend page 9, lines 25 – 26 as follows:

P can be $-C_6H_{4-n}F_n$ -(n = 0 to 4); $-C_6H_{4-n}F_n - CF_2-C_6H_{4-n}F$ -(n = 0 to 8); $-C_{10}H_{6-n}F_n$ -(n = 0 to 6), or $-C_{12}H_{8-n}F_n$ -(n = 0 to 8).

Please amend page 10, lines 1 – 7 as follows:

The benzocyclobutane-containing precursor can have the following general structure (IIa'):



wherein each W is W', W'', W''', W'''', and W''''' are independently the same or different and are fluorinate phenyl, -F or -H, n' is an integer of ~~at least 2 to a number that is less than total sp^2 C substitutions on P'~~, P' can be $-C_6H_{4-n}F_n$ - (n = 0 to 4); $-C_6H_{4-n}F_n-CF_2-C_6H_{4-n}F_n$ - (n = 0 to 8 4); $-C_{10}H_{6-n}F_n$ - (n = 0 to 6), or $-C_{12}H_{8-n}F_n$ - (n = 0 to 8).